

## 5 A High Voltage Schottky Barrier Rectifier

#### **DESCRIPTION**

This UPS5100e3 in the Powermite3® package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3® package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

**IMPORTANT:** For the most current data, consult *MICROSEMI*'s website: http://www.microsemi.com

#### **KEY FEATURES**

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

# ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

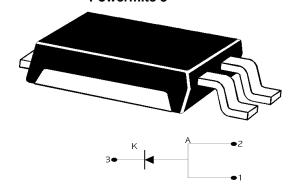
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}$	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Rectified Output Current	Io	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T <sub>c</sub> =90 °C	I <sub>FSM</sub>	100	А
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C
Junction Temperature	$T_J$	-55 to +125	°C

#### THERMAL CHARACTERISTICS

Thermal Resistance			
Junction-to-Case (bottom)	R <sub>eJC</sub>	2.5	°C/ Watt
Junction to Ambient (1)	Rain	65	°C/ Watt

(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print

### Powermite 3™



#### APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I<sub>RM</sub>
- Small foot print 190 X 260 mils (1:1 Actual size)
  See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S5100•
- WEIGHT: 0.072 gram (approx.)
- · Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel



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Parameter	Symbol	Conditions	Min	Тур.	Max	Units
· aramete.		001141110110		. , .	, max	• • • • • • • • • • • • • • • • • • • •
Forward Voltage (Note 1)	V <sub>F</sub>	$I_F = 5 \text{ A}$ , $T_L = 25 ^{\circ}\text{C}$ $I_F = 5 \text{ A}$ , $T_L = 125 ^{\circ}\text{C}$ $I_F = 10 \text{ A}$ , $T_L = 25 ^{\circ}\text{C}$ $I_F = 10 \text{ A}$ , $T_L = 125 ^{\circ}\text{C}$		0.75 0.58 0.84 0.67	0.81 0.64 0.90 0.73	٧
Reverse Break Down Voltage (Note 1)	$V_{BR}$	I <sub>R</sub> = 0.2 mA	100			V
Reverse Current (Note1)	I <sub>R</sub>	V <sub>R</sub> = 100V, T <sub>j</sub> = 25°C V <sub>R</sub> = 100V, T <sub>j</sub> = 125 °C		15 10	200 20	μA mA
Capacitance	Ст	V <sub>R</sub> = 4 V; f = 1 MH <sub>Z</sub>		150		pF

Note: 1 Short duration test pulse used to minimize self – heating effect.

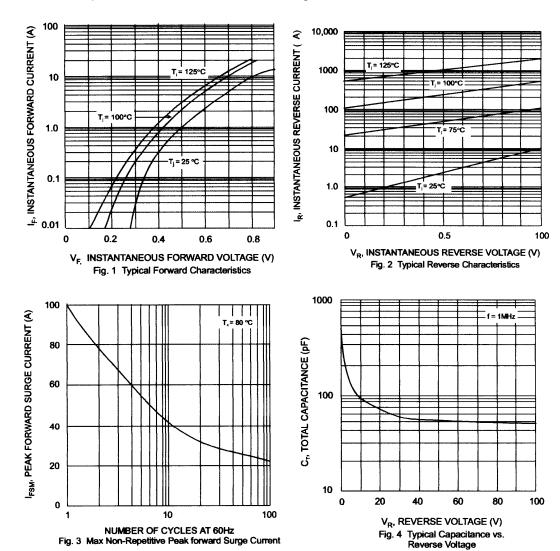
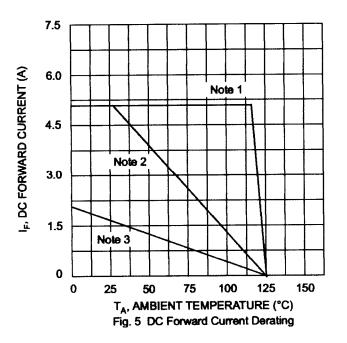
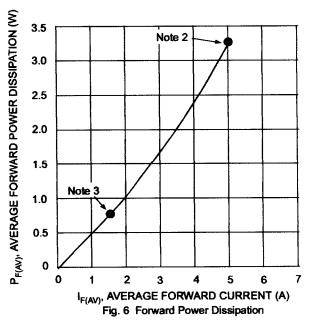


Fig. 3 Max Non-Repetitive Peak forward Surge Current



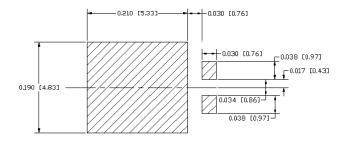
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- Notes: 1.  $T_A = T_{SOLDERING\ POINT}$ ,  $R_{\Theta JS} = 2.5 \text{C/W}$ ,  $R_{\Theta SA} = 0^{\circ} \text{C/W}$ .
  - 2. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R<sub>ΘJA</sub> in range of 20-35°C/W.
  - 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout  $R_{\Theta,IA}$  in range of 65°C/W. See mounting pad below.

## **MOUNTING PAD LAYOUT**

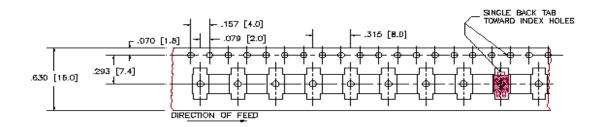


Mounting Pad Dimensions: inches [mm]

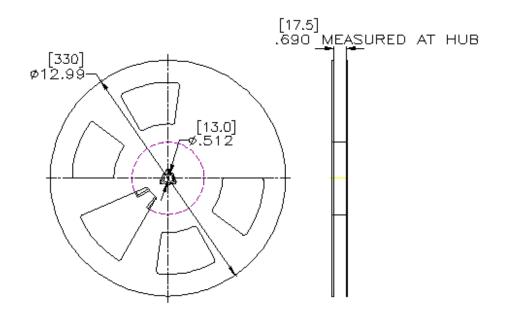


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### **TAPE & REEL**



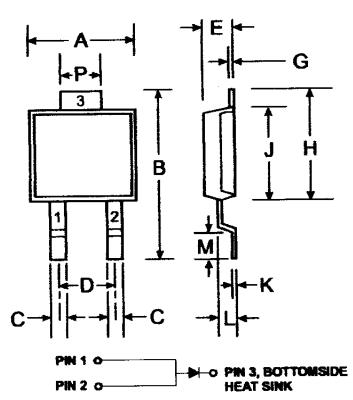
## 13 INCH REEL





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## **PACKAGE DIMENSIONS**



POWERMITE®3			
Dim	Min	Max	
A	4.03	4.09	
В	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
E	1.10	1.14	
G	.178 NOM		
Н	5.01	5.17	
J	4.37	4.43	
K	.178 NOM		
L	.71	.77	
M	.36	.46	
P	1.73	1.83	
All Dimensions in mm			

Note:

Pins 1 & 2 must be electrically connected at the printed circuit board.

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